

# Transistors

## 2SA642

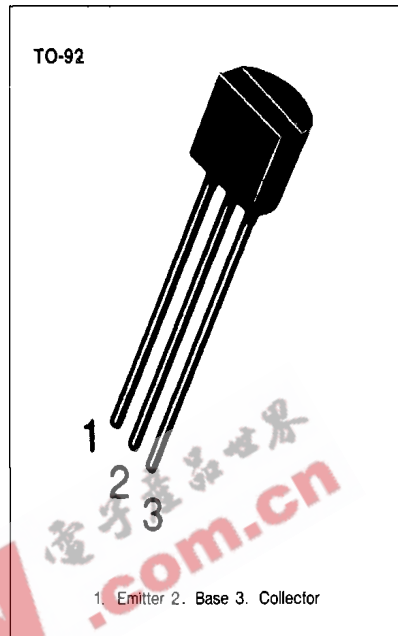
### LOW FREQUENCY POWER AMPLIFIER

- Collector Dissipation  $P_C=400\text{mW}$

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	- 30	V
Collector-Emitter Voltage	$V_{CEO}$	- 25	V
Emitter-Base Voltage	$V_{EBO}$	- 5	V
Collector Current (DC)	$I_C$ (DC)	- 300	mA
Collector Current (pulse)	$I_C$ (pulse)*	- 500	mA
Collector Dissipation	$P_C$	400	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 ~ 150	$^\circ\text{C}$

\*  $PW \leq 10\text{ms}$ , duty cycle  $\leq 50\%$



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -100\mu\text{A}$ , $I_E = 0$	- 30			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -10\text{mA}$ , $I_B = 0$	- 25			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -10\mu\text{A}$ , $I_C = 0$	- 5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -25\text{V}$ , $I_E = 0$			- 100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -3\text{V}$ , $I_C = 0$			- 100	nA
DC Current Gain	$h_{FE}$	$V_{CE} = -1\text{V}$ , $I_C = -50\text{mA}$ *	70		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -300\text{mA}$ , $I_B = -30\text{mA}$ *		- 0.35	- 0.6	V

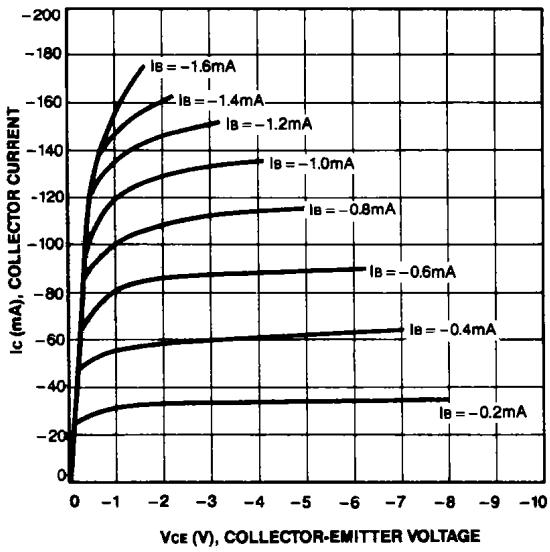
\* Pulse Test:  $PW \leq 350\mu\text{s}$ , duty cycle  $\leq 2\%$

### $h_{FE}$ CLASSIFICATION

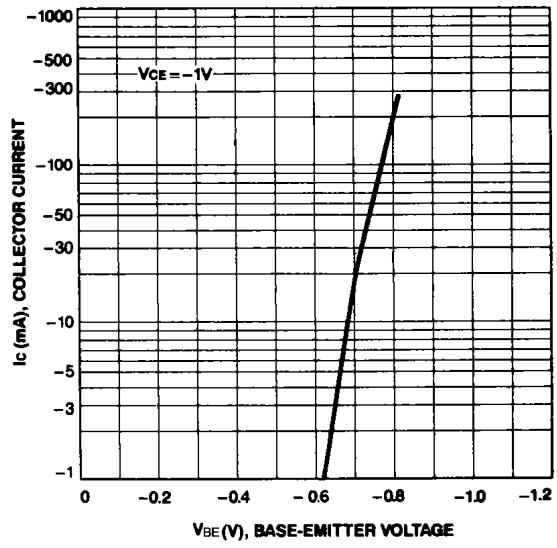
Classification	O	Y	G
$h_{FE}$	70-140	120-240	200-400



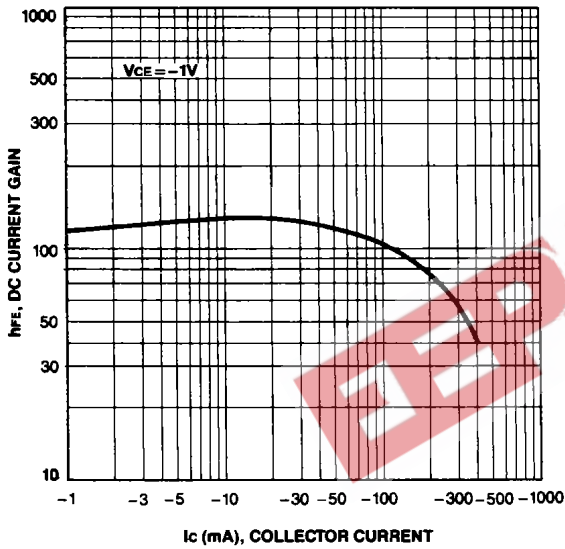
**STATIC CHARACTERISTIC**



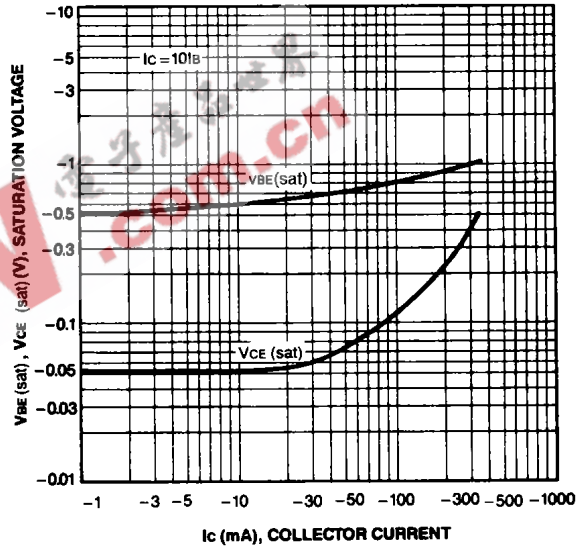
**BASE-EMITTER ON VOLTAGE**



**DC CURRENT GAIN**



**BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE**



**COLLECTOR OUTPUT CAPACITANCE**

